TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

2SC4738

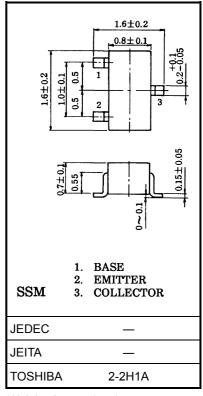
Audio Frequency General Purpose Amplifier Applications

Unit: mm

- $\bullet~$ High voltage and high current: $V_{\rm CEO}$ = 50 V, $I_{\rm C}$ = 150 mA (max)
- Excellent hFE linearity: hFE (IC = 0.1 mA)/ hFE (IC = 2 mA) = 0.95 (typ.)
- High h_{FE}: $h_{FE} = 120 \sim 700$
- Complementary to 2SA1832
- Small package

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	V _{CEO}	50	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	Ic	150	mA
Base current	Ι _Β	30	mA
Collector power dissipation	P _C	100	mW
Junction temperature	Tj	125	°C
Storage temperature range	T _{stg}	-55~125	°C



Weight: 2.4 mg (typ.)

Electrical Characteristics (Ta = 25°C)

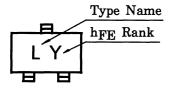
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = 60 V, I _E = 0	_	_	0.1	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} = 5 V, I _C = 0	_	_	0.1	μА
DC current gain	h _{FE} (Note)	$V_{CE} = 6 \text{ V}, I_C = 2 \text{ mA}$	120	_	700	
Collector-emitter saturation voltage	V _{CE} (sat)	$I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$	_	0.1	0.25	V
Transition frequency	f _T	V _{CE} = 10 V, I _C = 1 mA	80	_	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz	_	2.0	3.5	pF

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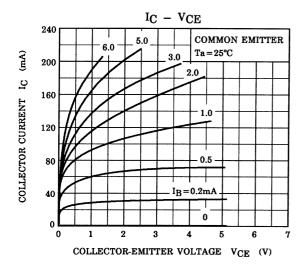
Note: hFE classification Y (Y): 120~240, GR (G): 200~400, BL (L): 350~700

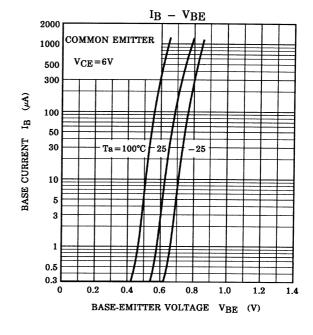
() marking symbol

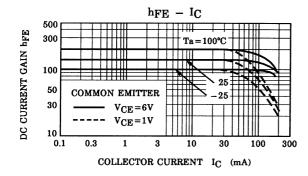
Marking

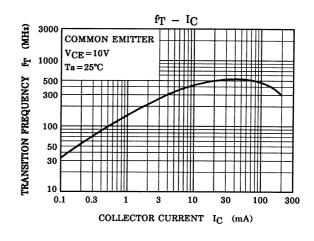


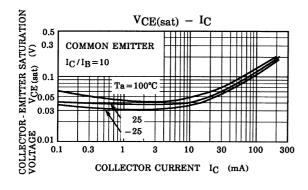
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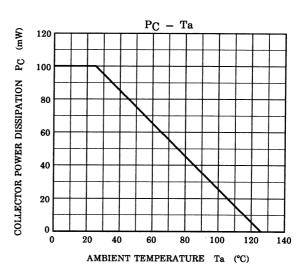


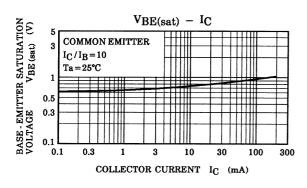












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